

CW lasing of current injection blue GaN-based vertical c

Applied Physics Letters

92,

DOI: 10.1063/1.2908034

Citation Report

#	ARTICLE	IF	CITATIONS
1	High-reflectivity ultraviolet AlN/AlGa _N distributed Bragg reflectors grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2008, 310, 4871-4875.	1.5	11
2	Room temperature polariton lasing in a GaN/AlGa _N multiple quantum well microcavity. Applied Physics Letters, 2008, 93, .	3.3	267
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